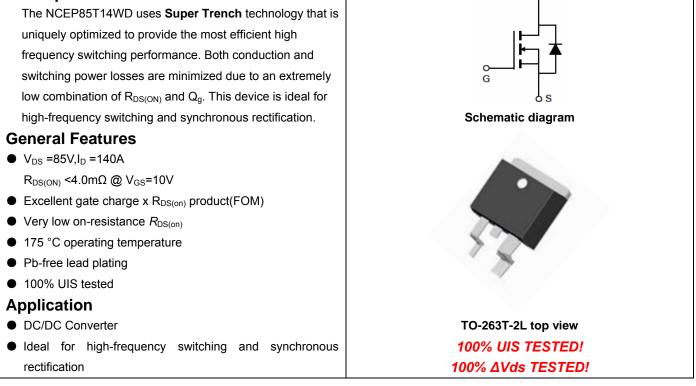




Q D

NCE N-Channel Super Trench Power MOSFET

Description



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP85T14WD	NCEP85T14WD	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	85	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	140	А
Drain Current-Continuous(Tc=100℃)	I _D (100℃)	99	А
Pulsed Drain Current	I _{DM}	420	А
Maximum Power Dissipation	PD	200	W
Derating factor		1.3	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	1000	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	0.75	°C /W





NCEP85T14WD

Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	····					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =85V, V_{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	····			•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.0	3.1	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I _D =70A	-	3.3	4.0	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =70A	50	-	-	S
Dynamic Characteristics (Note4)	· ·		-			
Input Capacitance	C _{lss}	<u>)</u> () () () (-	5600	-	PF
Output Capacitance	C _{oss}	V _{DS} =40V,V _{GS} =0V, F=1.0MHz	-	850	-	PF
Reverse Transfer Capacitance	C _{rss}		-	60	-	PF
Switching Characteristics (Note 4)	· · · · ·		-			
Turn-on Delay Time	t _{d(on)}		-	20	-	nS
Turn-on Rise Time	tr	V _{DD} =40V,I _D =70A	-	10	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =4.7 Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	35	-	nS
Total Gate Charge	Qg	V -40V(1 -70A	-	84		nC
Gate-Source Charge	Q _{gs}	V _{DS} =40V,I _D =70A, V _{GS} =10V	-	30.6		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	18.5		nC
Drain-Source Diode Characteristics	· ·			•		
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =140A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	140	А
Reverse Recovery Time	t _{rr}	T_J = 25°C, I_F = I_S	-	83		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	194		nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^\circ C$,V_{DD}=42.5V,V_G=10V,L=0.5mH,Rg=25\Omega

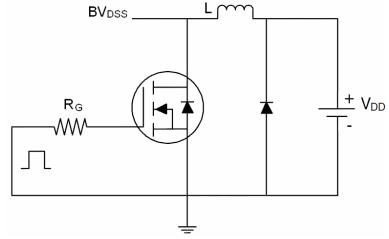


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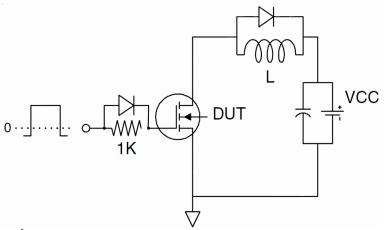
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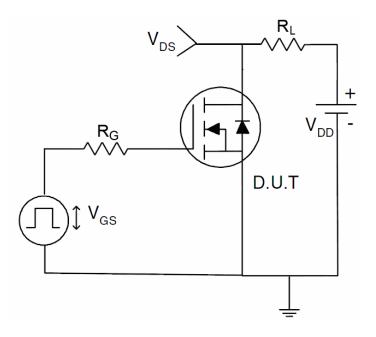
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit

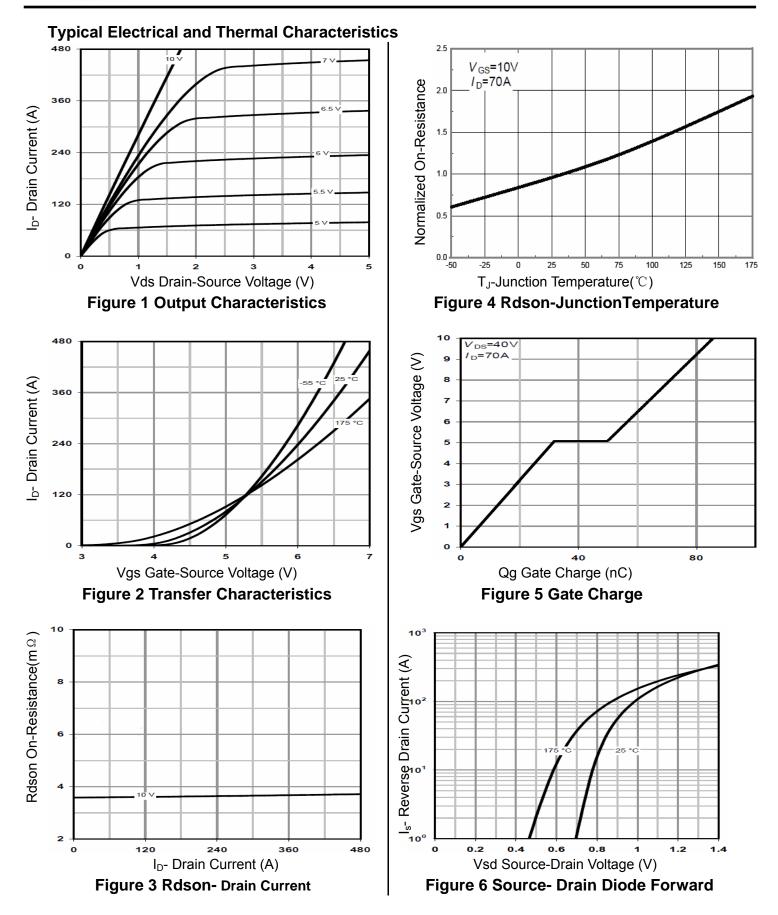




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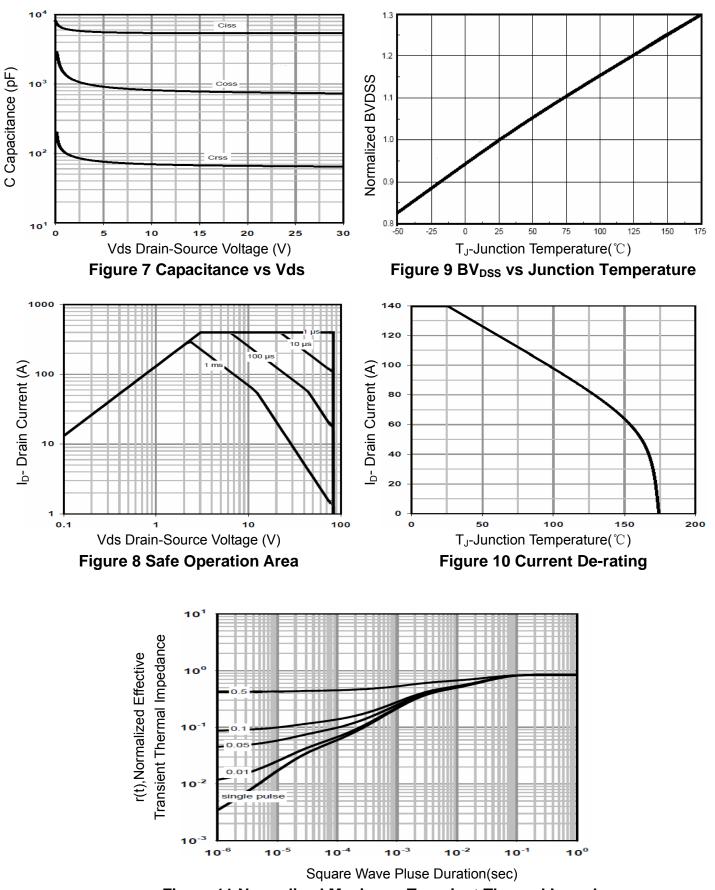




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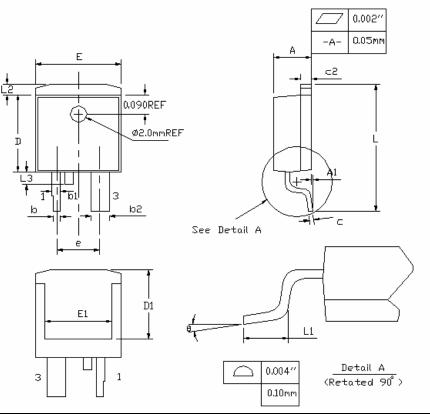




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TO-263T-2L Package Information



Symbol	Dimension	s In Inches	Dimensions In Millimeters		
	Min.	Max.	Min.	Max.	
A	0.170	0.180	4.32	4.57	
A1	-	0.010	-	0.25	
b	0.028	0.037	0.71	0.94	
b 1	0.035	0.047	0.9	1.2	
b2	0.081	0.095	2.05	2.4	
С	0.018	0.024	0.46	0.61	
c2	0.048	0.055	1.22	1.40	
D	0.350	0.370	8.89	9.40	
D1	0.315	0.324	8.01	8.23	
E	0.395	0.405	10.04	10.28	
E1	0.310	0.318	7.88	8.08	
е	0.200	0.200 BSC.		BSC.	
L	0.580	0.620	14.73	15.75	
L1	0.090	0.110	2.29	2.79	
L2	0.045	0.055	1.15	1.39	
L3	0.050	0.070	1.27	1.77	
θ	0°	8°	0°	8°	







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